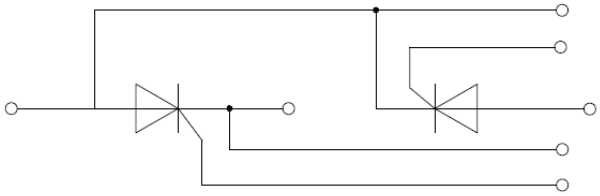
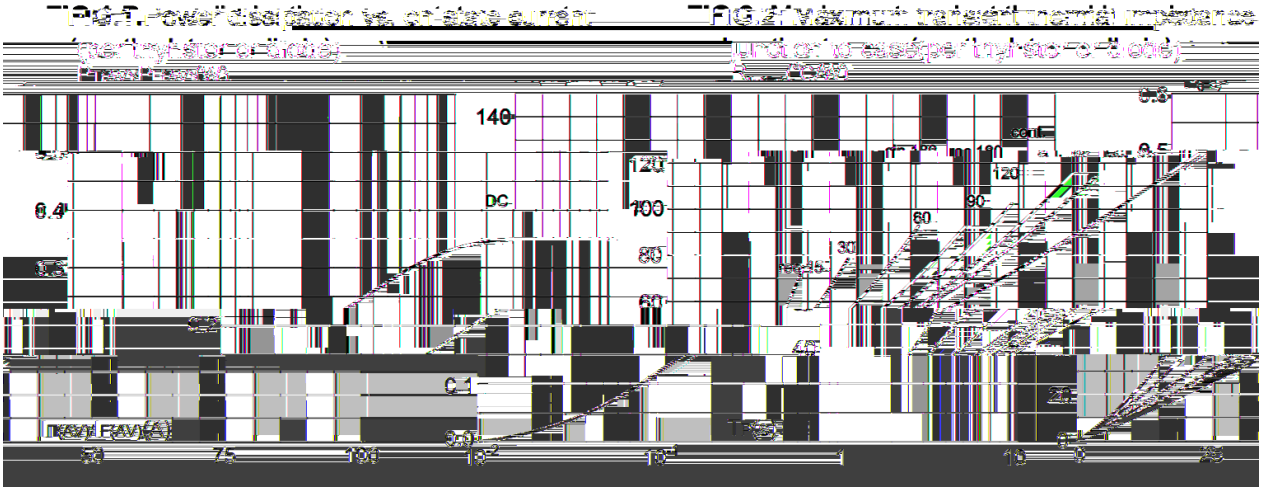
℃		



	℃			
				℃
				℃



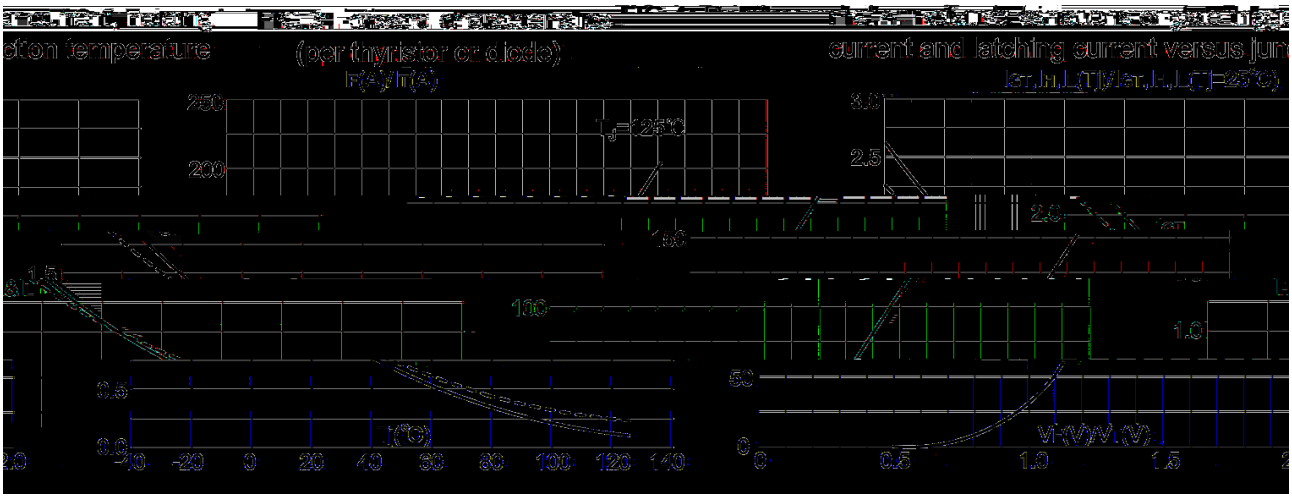


FIG.5 Gate trigger characteristics

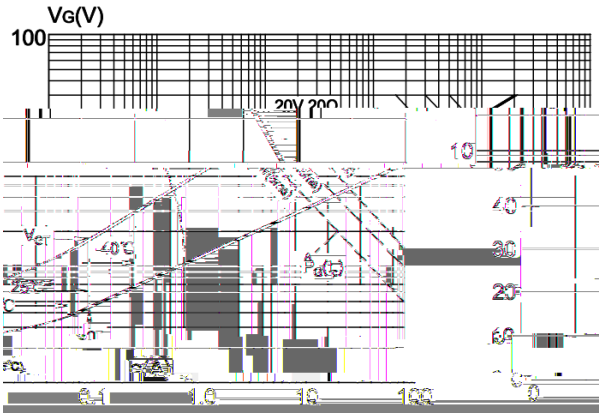
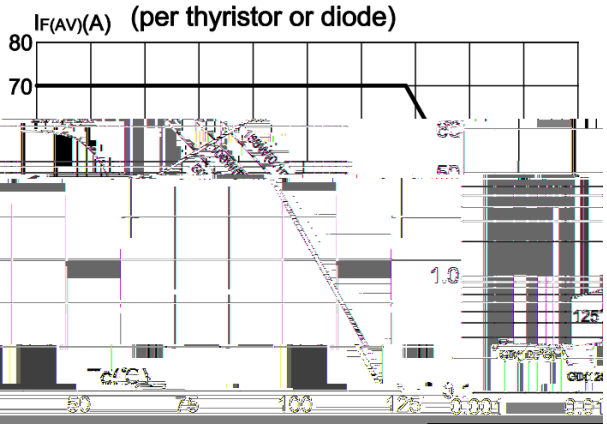
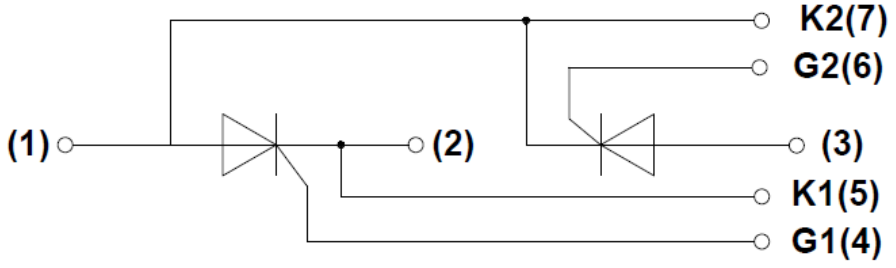
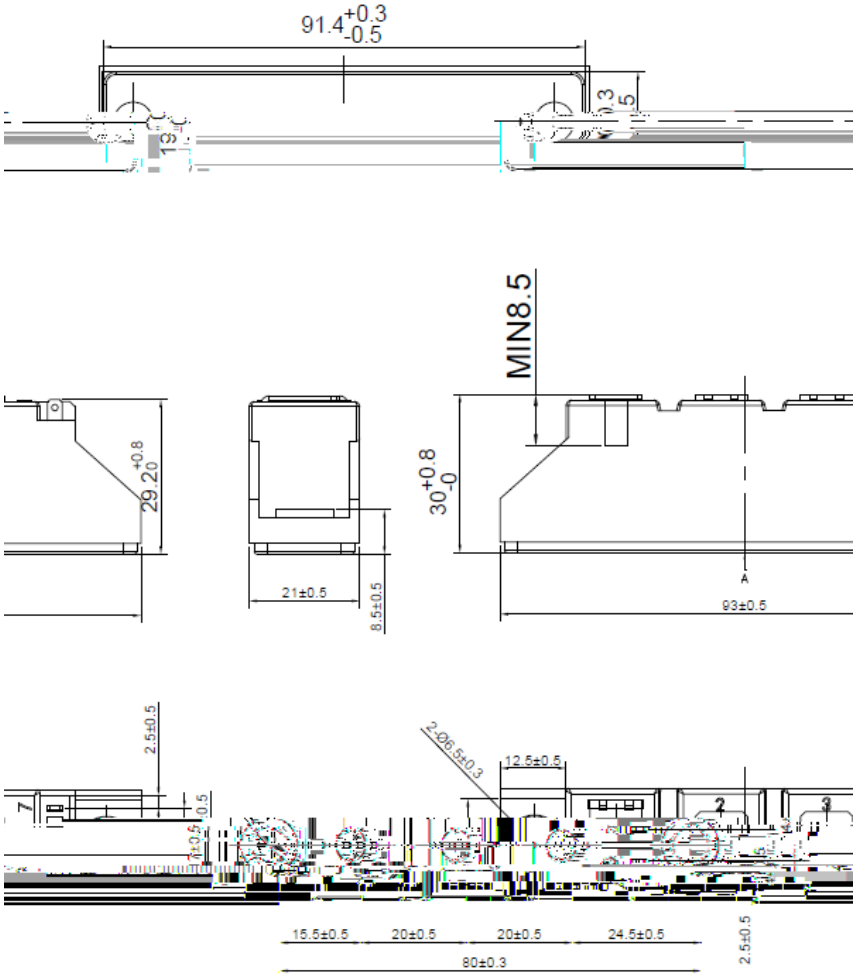


FIG.6: Forward current vs. case temperature (per thyristor or diode)




K2(7)
G2(6)
(1)
(2)
(3)
K1(5)
G1(4)


91.4+0.3 -0.5
MIN8.5
29.2+0.8 -0
30+0.8 -0
21±0.5
8.5±0.5
93±0.5
A
2.5±0.5
2-Ø6.5±0.3
12.5±0.5
15.5±0.5
20±0.5
20±0.5
24.5±0.5
80±0.3
2.5±0.5